



RN1971TE85LF Information



For Reference Only

Part Number RN1971TE85LF

Manufacturer Toshiba Semiconductor and Storage Category Discrete Semiconductor Products

Transistors - Bipolar (BJT) - Arrays, Pre-Biased

Description TRANS 2NPN PREBIAS 0.2W US6

Package 6-TSSOP, SC-88, SOT-363
For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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RN1971TE85LF Specifications

Manufacturer Part NumberRN1971TE85LFManufacturerToshiba Semiconductor and StorageCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - Arrays, Pre-BiasedPackage6-TSSOP, SC-88, SOT-363Series-Transistor Type2 NPN - Pre-Biased (Dual)Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)-Resistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Ic, Vce120 @ ImA, 5VVce Saturation (Max) @ Ib, Ic300mV @ 250μA, 5mACurrent - Collector Cutoff (Max)100nA (ICBO)Frequency - Transition250MHzPower - Max200mWMounting TypeSurface MountPackage / Case6-TSSOP, SC-88, SOT-363Supplier Device PackageUS6	•	
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Resistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Ic, Vce120 @ 1mA, 5VVce Saturation (Max) @ Ib, Ic300mV @ 250μA, 5mACurrent - Collector Cutoff (Max)100nA (ICBO)Frequency - Transition250MHzPower - Max200mWMounting TypeSurface MountPackage / Case6-TSSOP, SC-88, SOT-363Supplier Device PackageUS6	Voltage - Collector Emitter Breakdown (Max)	50V
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Supplier Device Package US6	Mounting Type	Surface Mount
	Package / Case	6-TSSOP, SC-88, SOT-363
	Supplier Device Package	US6
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RN1971TE85LF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

RN1971TE85LF Payment Methods



















RN1971TE85LF Shipping Methods













If you have any question about RN1971TE85LF, please do not hesitate to contact us!

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